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(54) **DRIVE VOLTAGE GENERATOR**

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(57) **ABSTRACT**

According to an aspect of the present disclosure, a drive voltage generator for driving a GaN high electron mobility transistor is provided. According to another aspect there is provided a GaN high electron mobility transistor unit including a GaN high electron mobility transistor, and a drive voltage generator connected to the GaN high electron mobility transistor. A method for generating a drive voltage for a GaN high electron mobility transistor is also provided.

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